Notification about the transfer of the semiconductor business

The semiconductor business of Panasonic Corporation was transferred on September 1, 2020 to Nuvoton Technology Corporation (hereinafter referred to as "Nuvoton"). Accordingly, Panasonic Semiconductor Solutions Co., Ltd. became under the umbrella of the Nuvoton Group, with the new name of Nuvoton Technology Corporation Japan (hereinafter referred to as "NTCJ").

In accordance with this transfer, semiconductor products will be handled as NTCJ-made products after September 1, 2020. However, such products will be continuously sold through Panasonic Corporation.

Publisher of this Document is NTCJ.

If you would find description "Panasonic" or "Panasonic semiconductor solutions", please replace it with NTCJ.

* Except below description page

"Request for your special attention and precautions in using the technical information and semiconductors described in this book"

Nuvoton Technology Corporation Japan



FC4B21280L

MOS FET FC4B21280L

Gate resistor installed Dual N-channel MOS FET

For lithium-ion secondary battery protection circuits

Features

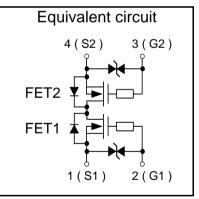
- Source-source On-state Resistance : RSS(on) typ. = 17 mΩ (VGS = 3.8 V)
- CSP (Chip Size Package)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL : Level 1)
- Marking Symbol : 27

Packaging

Embossed type (Thermo-compression sealing): 20 000 pcs / reel (standard)

Absolute Maximum Ratings Ta = 25 °C								
Parameter		Symbol	Rating	Unit				
Source-source Voltage		VSS	12	V				
Gate-source Voltage		VGS	±8	V				
Source Current		IS1 *1	4.0	А				
	DC	IS2 ^{*2}	6.6					
		IS3 ^{*3}	8.9	A				
	Pulsed *4	ISp	40					
Total Power Dissipation	DC	PD1 *1	0.36	W				
		PD2 *2	1.0					
		PD3 *3	1.8					
Channel Temperature		Tch	150	°C				
Storage Temperature Range		Tstg	-55 to +150	°C				

Unit: mm 1.11 £ (Top View) 2 Mark Identifie 0.10 (Front View) Φ0.25 0.5 (Bottom View) 305) (0.305) 0.5 1. Source1 (FET1) 2. Gate1 (FET1) 3. Gate2 (FET2) 4. Source2 (FET2) ULGA004-W-1212 Panasonic JEITA Code



_____ Rth3 ^{*3} _____ Note *1 Mounted on FR4 board (25.4 mm × 25.4 mm × t1.0 m

te *1 Mounted on FR4 board (25.4 mm \times 25.4 mm \times t1.0 mm). FR4 board partially covered with copper pad (18 mm² area, 36 μ m thickness).

*2 Mounted on FR4 board ($25.4 \text{ mm} \times 25.4 \text{ mm} \times 11.0 \text{ mm}$).

FR4 board fully covered with copper pad. (613 mm² area, 36 μ m thickness).

Symbol

Rth1

Rth2

Rating

347

125

69

Unit

°C/W

*3 Mounted on ceramic board ($70 \text{ mm} \times 70 \text{ mm} \times t1.0 \text{ mm}$).

*4 t = 10 $\mu s,$ Duty Cycle \leq 1 %.

■ Thermal Characteristics Ta = 25 °C

Parameter

Thermal Resistance (ch-a)



MOS FET

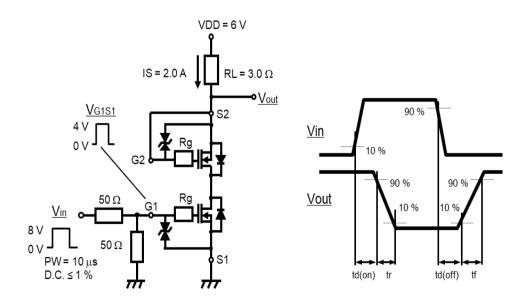
\blacksquare Electrical Characteristics $Ta = 25^{\circ}$				-			
Parameter	Symbol	Conditions	Min	Тур	Max	Unit	
Source-source Breakdown Voltage	VSSS	IS = 1 mA, VGS = 0 V	12			V	
Zero Gate Voltage Source Current	ISSS	VSS = 12 V, VGS = 0 V			1.0	μΑ	
Gate-source Leakage Current	IGSS1	$VGS = \pm 8 V, VSS = 0 V$			±1.0	μΑ	
	IGSS2	$VGS = \pm 3.8 V, VSS = 0 V$			±0.1	μΑ	
Gate-source Threshold Voltage	Vth	IS = 0.2 mA, VSS = 6 V	0.35	0.9	1.4	V	
Source-source On-state Resistance	RSS(on)1	IS = 2.0 A, VGS = 4.5 V	12	16	21		
	RSS(on)2	IS = 2.0 A, VGS = 4.1 V	12.5	16.5	21.5	mΩ	
	RSS(on)3	IS = 2.0 A, VGS = 4.0 V	12.5	16.5	21.5		
	RSS(on)4	IS = 2.0 A, VGS = 3.8 V	13	17	22.5		
	RSS(on)5	IS = 2.0 A, VGS = 3.7 V	13	17.5	23.5		
	RSS(on)6	IS = 2.0 A, VGS = 3.1 V	13.5	19	31		
	RSS(on)7	IS = 2.0 A, VGS = 2.5 V	14	23	45		
Body Diode Forward Voltage	VF(s-s)	IF = 2.0 A, VGS = 0 V		0.7	1.0	V	
Input Capacitance ^{*1}	Ciss			670			
Output Capacitance *1	Coss	VSS = 10 V, VGS = 0 V, f = 1 kHz		129		pF	
Reverse Transfer Capacitance *1	Crss			90			
Turn-on Delay Time *1,*2	td(on)	VDD = 6 V, VGS = 0 to 4 V		0.19		-	
Rise Time ^{*1,*2}	tr	IS = 2.0 A 0.3		0.38		μS	
Turn-off Delay Time *1,*2	td(off)	VDD = 6 V, VGS = 4 to 0 V		0.93			
Fall Time *1,*2	tf	IS = 2.0 A		0.56		μS	
Total Gate Charge ^{*1}	Qg	VDD = 6 V		6.2			
Gate-source Charge *1	Qgs	VGS = 0 to 4 V		1.6		nC	
Gate-drain Charge ^{*1}	Qgd	IS = 4.0 A		1.1			

■ Electrical Characteristics Ta = 25 °C ± 3 °C

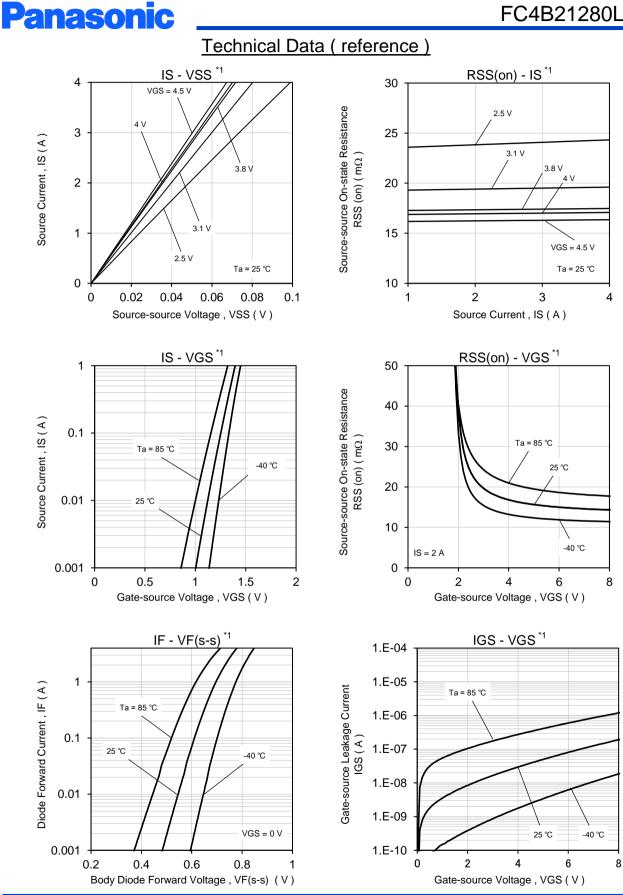
Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

*1 Guaranteed by design, not subject to production testing.

*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time.



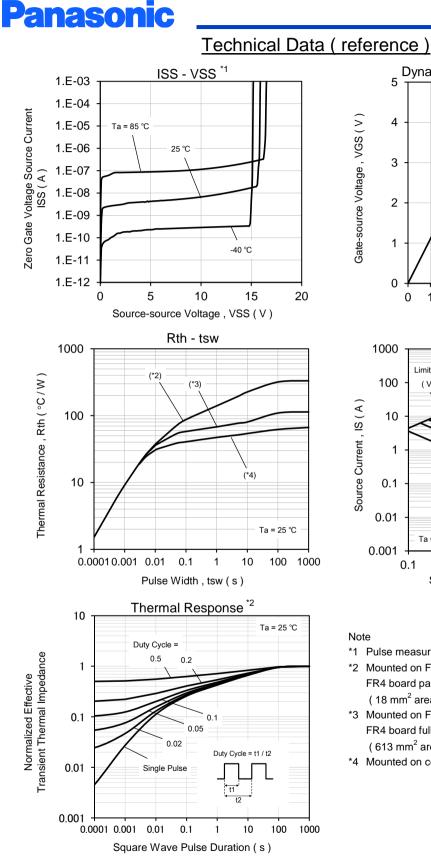
MOS FET FC4B21280L

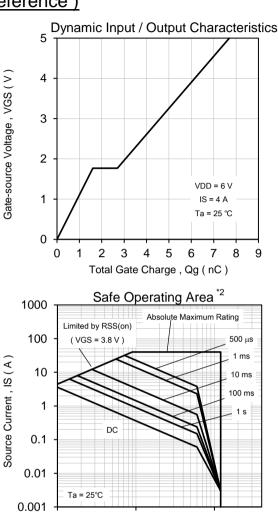


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MOS FET FC4B21280L





*1 Pulse measurement.

0.1

*2 Mounted on FR4 board ($25.4 \text{ mm} \times 25.4 \text{ mm} \times t1.0 \text{ mm}$) FR4 board partially covered with copper pad (18 mm^2 area, $36 \mu \text{m}$ thickness).

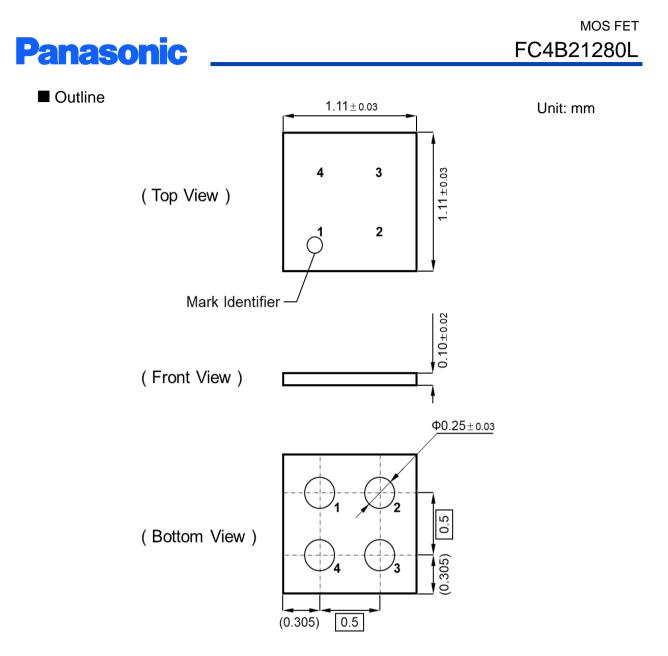
1

Source-source Voltage, VSS (V)

10

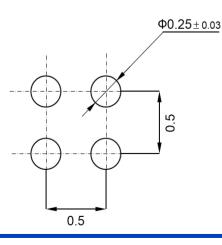
- *3 Mounted on FR4 board (25.4 mm \times 25.4 mm \times t1.0 mm) FR4 board fully covered with copper pad (613 mm² area, 36 μ m thickness).
- *4 Mounted on ceramic board ($70 \text{ mm} \times 70 \text{ mm} \times t1.0 \text{ mm}$).

Doc No. TD4-ZZ-01815 Revision. 0



Land & Stencil Pattern (reference)

Unit: mm



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Established : 2020-06-10 Revised : ####-##

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